Vanguard Semiconductor

VSP050N15HS

150V/35A N-Channel Advanced Power MOSFET

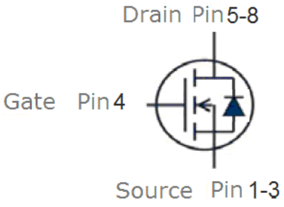
V_{DS}	150	V
$R_{DS(on),TYP}$@ V_{GS}=10 V	35	mΩ
I_D	35	A

Features

- N-Channel，10V Logic level control
- Enhancement mode
- Fast Switching
- Very low on-resistance $R_{DS(on)}$
- 100% Avalanche test
- Pb-free lead plating; RoHS compliant

Pb-Free RoHS HF Halogen-Free

PDFN5x6



Part ID	Package Type	Marking	Tape and reel information
VSP050N15HS	PDFN5x6	050N15H	3000pcs/Reel

Maximum ratings, at T_j=25 °C, unless otherwise specified

Symbol	Parameter		Rating	Unit
Common Ratings (Tc=25°C Unless Otherwise Noted)				
V_{GS}	Gate-Source Voltage		±20	V
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage		150	V
T_J	Maximum Junction Temperature		150	°C
T_{STG}	Storage Temperature Range		-55 to 150	°C
I_S	Diode Continuous Forward Current	T_C =25°C	35	A
Mounted on Large Heat Sink				
I_D	Continuous Drain current@VGS=10V	T_C =25°C	35	A
		T_C =100°C	22	A
I_{DM}	Pulse Drain Current Tested ①	T_C =25°C	100	A
P_D	Maximum Power Dissipation	T_C =25°C	83	W
$R_{\theta JC}$	Thermal Resistance-Junction to Case		1.5	°C/W
$R_{\theta JA}$	Thermal Resistance Junction-Ambient		52.5	°C/W
Drain-Source Avalanche Ratings				
EAS	Avalanche Energy, Single Pulsed ②		169	mJ

Symbol	Parameter	Condition	Min.	Typ.	Max.	Unit
Static Electrical Characteristics @ T_j = 25°C (unless otherwise stated)						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}=0V I_D=250μA	150	--	--	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=150V,V_{GS}=0V	--	--	1	μA
	Zero Gate Voltage Drain Current(T_j=125℃)	V_{DS}=150V,V_{GS}=0V	--	--	100	μA
I_{GSS}	Gate-Body Leakage Current	V_{GS}=±20V,V_{DS}=0V	--	--	±100	nA
$V_{GS(TH)}$	Gate Threshold Voltage	V_{DS}=V_{GS},I_D=250μA	2.0	3.0	4.0	V
$R_{DS(ON)}$	Drain-Source On-State Resistance③	V_{GS}=10V, I_D=25A	--	35	50	mΩ
Dynamic Electrical Characteristics @ T_j= 25°C (unless otherwise stated)						
C_{iss}	Input Capacitance	V_{DS}=30V,V_{GS}=0V, f=1MHz	--	4950	--	pF
C_{oss}	Output Capacitance		--	165	--	pF
C_{rss}	Reverse Transfer Capacitance		--	65	--	pF
Q_g	Total Gate Charge	V_{DS}=75V,I_D=10A, V_{GS}=10V	--	46	--	nC
Q_{gs}	Gate-Source Charge		--	15	--	nC
Q_{gd}	Gate-Drain Charge		--	13	--	nC
Switching Characteristics						
$t_{d(on)}$	Turn-on Delay Time	V_{DD}=75V, I_D=10A, R_G=6.8Ω, V_{GS}=10V	--	22	--	nS
t_r	Turn-on Rise Time		--	11	--	nS
$t_{d(off)}$	Turn-Off Delay Time		--	38	--	nS
t_f	Turn-Off Fall Time		--	14	--	nS
Source- Drain Diode Characteristics@ T_j = 25°C (unless otherwise stated)						
V_{SD}	Forward on voltage	I_{SD}=25A,V_{GS}=0V	--	0.84	1.20	V
t_{rr}	Reverse Recovery Time	T_j=25℃,I_{sd}=10A, V_{GS}=0V di/dt=100A/μs	--	50	--	nS
Q_{rr}	Reverse Recovery Charge			385		nC

NOTE:

① Repetitive rating; pulse width limited by max. junction temperature.

② Limited by T_{Jmax}, starting T_J = 25°C, L = 0.5mH,R_G = 25Ω, I_{AS} = 26A, V_{GS} =10V. Part not recommended for use above this value

③ Pulse width ≤ 300μs; duty cycle≤ 2%.

Typical Characteristics

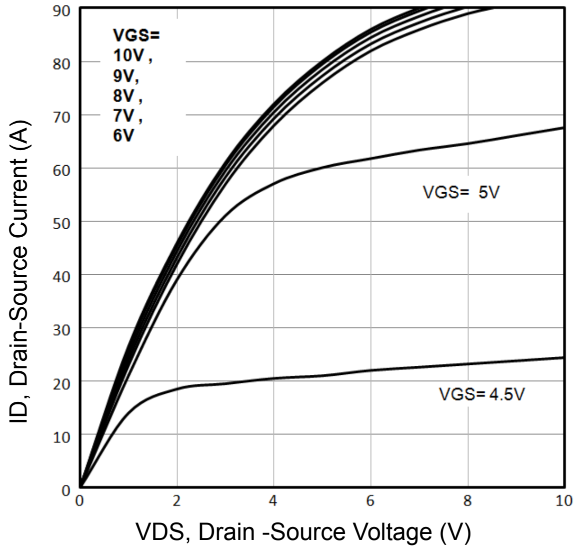


Fig1. Typical Output Characteristics

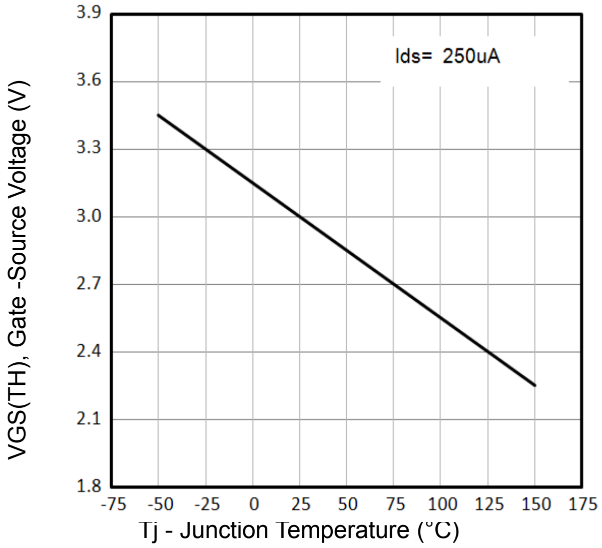


Fig2. $V_{GS(TH)}$ Gate -Source Voltage Vs.Tj

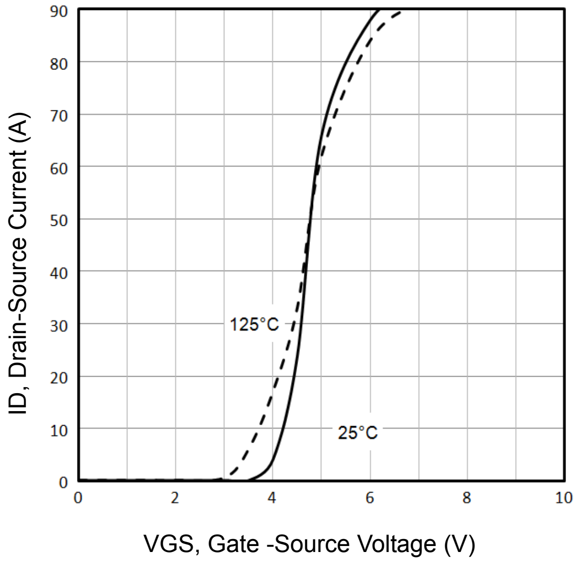


Fig3. Typical Transfer Characteristics

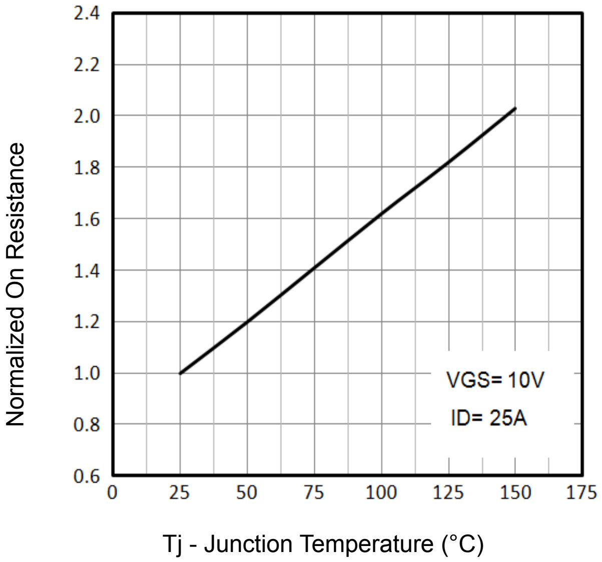


Fig4. Normalized On-Resistance Vs. Temperature

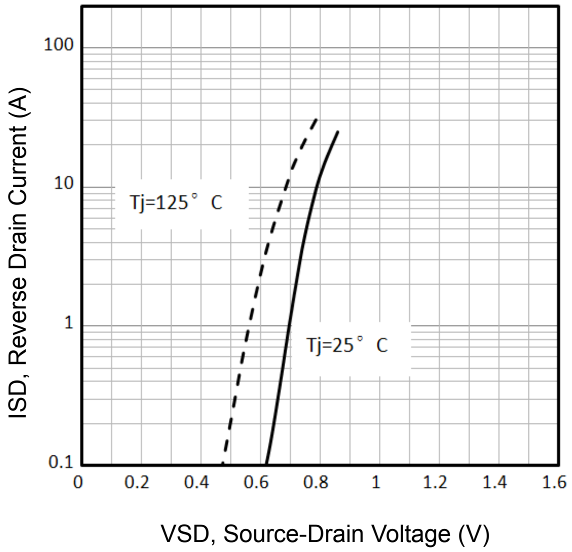


Fig5. Typical Source-Drain Diode Forward Voltage

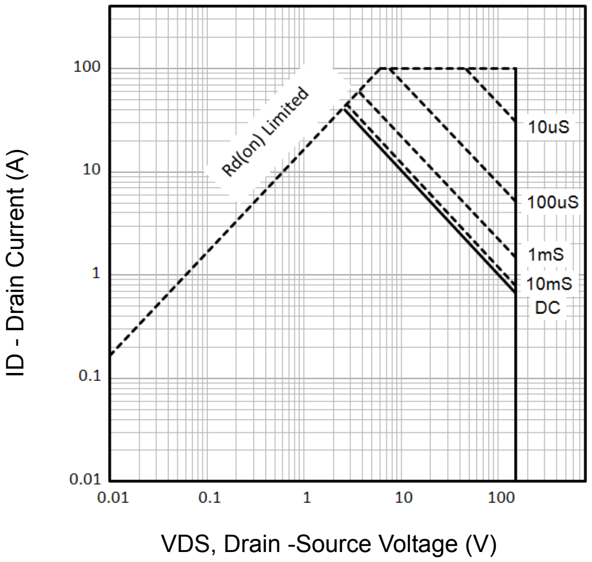


Fig6. Maximum Safe Operating Area

Typical Characteristics

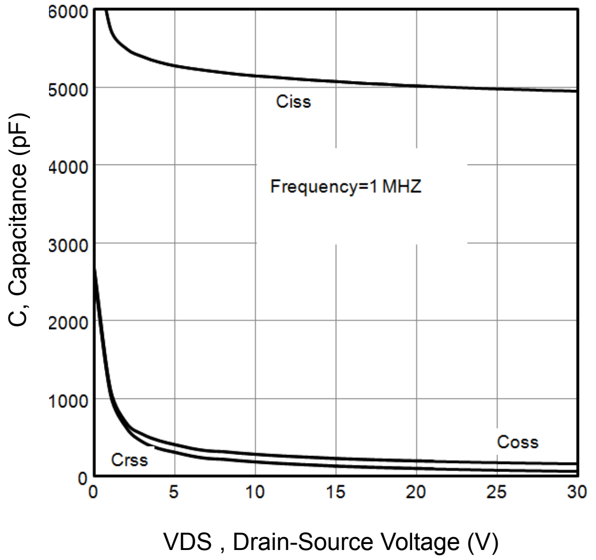


Fig7. Typical Capacitance Vs.Drain-Source Voltage

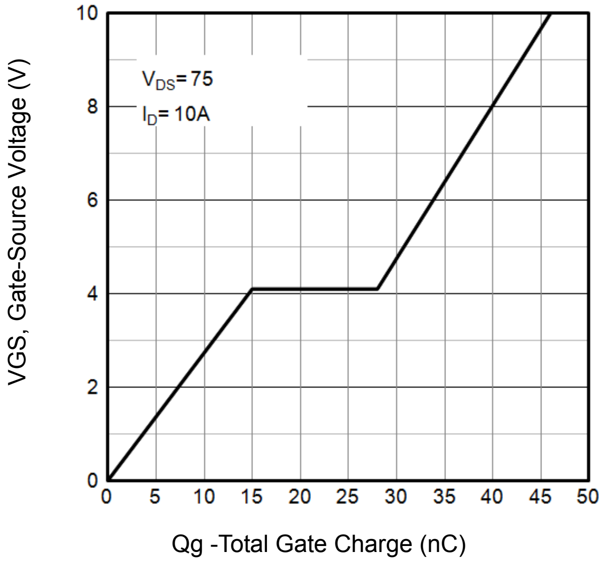


Fig8. Typical Gate Charge Vs.Gate-Source Voltage

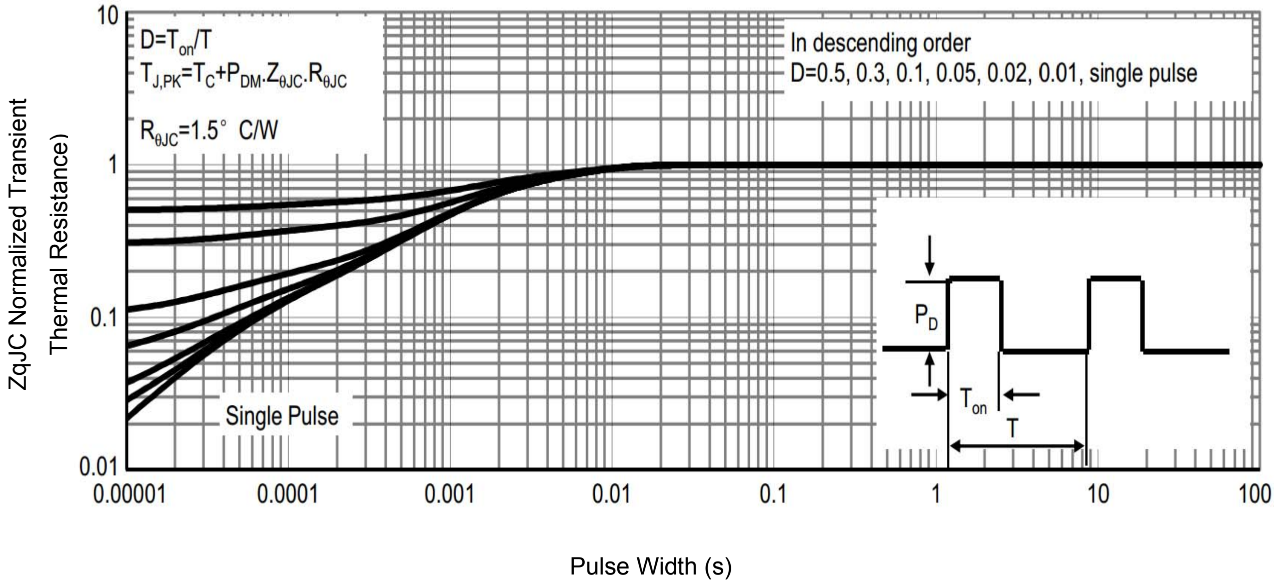


Fig9. Normalized Maximum Transient Thermal Impedance

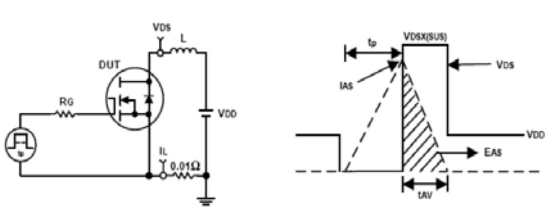


Fig10. Unclamped Inductive Test Circuit and waveforms

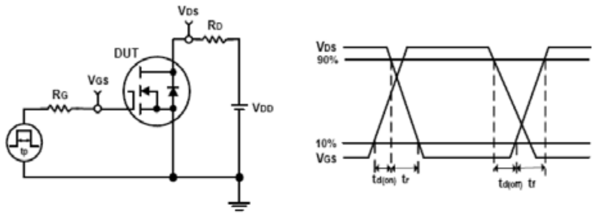
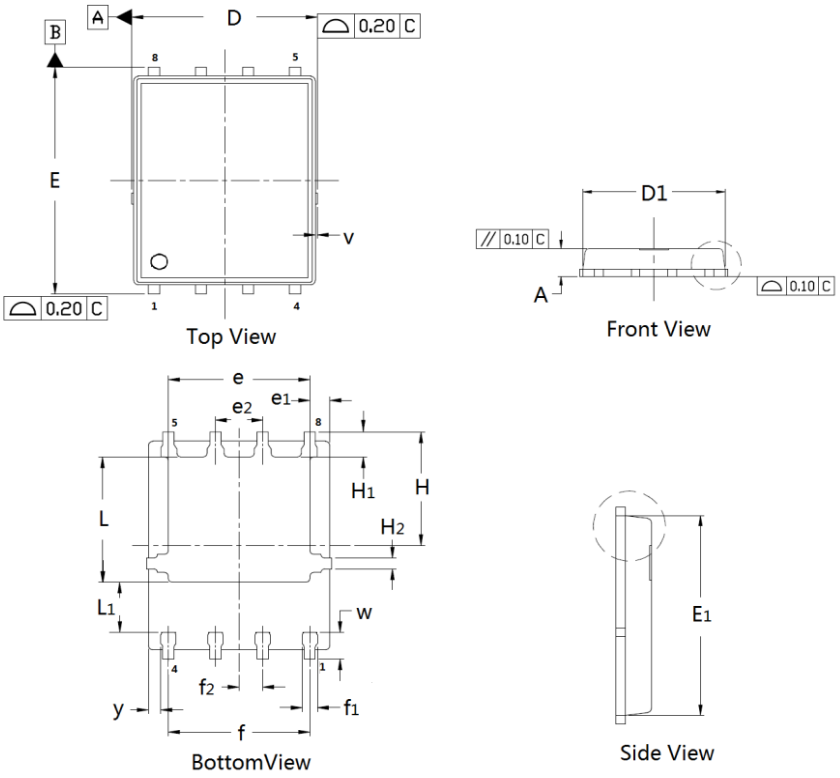


Fig11. Switching Time Test Circuit and waveforms

PDFN5×6 Package Outline Data



DIMENSIONS (unit : mm)

Symbol	Min	Typ	Max	Symbol	Min	Typ	Max
A	0.90	1.02	1.10	**D**	4.90	4.98	5.10
D_1	4.80	4.89	5.00	**E**	6.00	6.11	6.20
E_1	5.65	5.74	5.85	**e**	3.72	3.80	3.92
e_1	--	0.54	--	**e_2**	--	1.27	--
f	--	3.82	--	**f_1**	0.31	0.37	0.51
f_2	--	0.64	--	**H**	--	3.15	--
H_1	0.59	0.63	0.79	**H_2**	0.26	0.28	0.32
L	3.38	3.45	3.58	**L_1**	--	1.39	--
v	--	0.13	--	**w**	0.64	0.68	0.84
y	--	0.34	--		--		--

Customer Service

Sales and Service:

sales@vgsemi.com

Vanguard Semiconductor CO., LTD
TEL: (86-755) -26902410
FAX: (86-755) -26907027
WEB: www.vgsemi.com